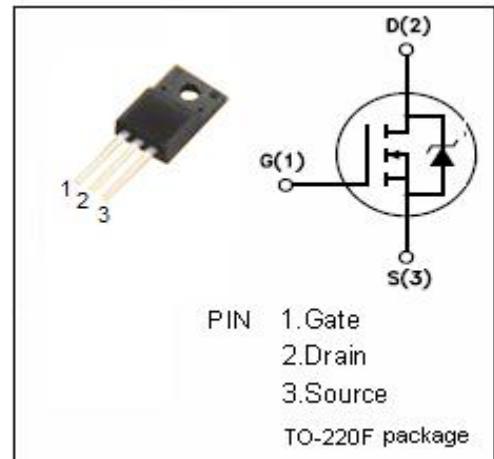


N-Channel MOSFET Transistor

2SK1766

DESCRIPTION

- Drain Current $I_D = 10A @ T_C=25^\circ C$
- Drain Source Voltage : $V_{DSS} = 250V$ (Min)
- Fast Switching Speed

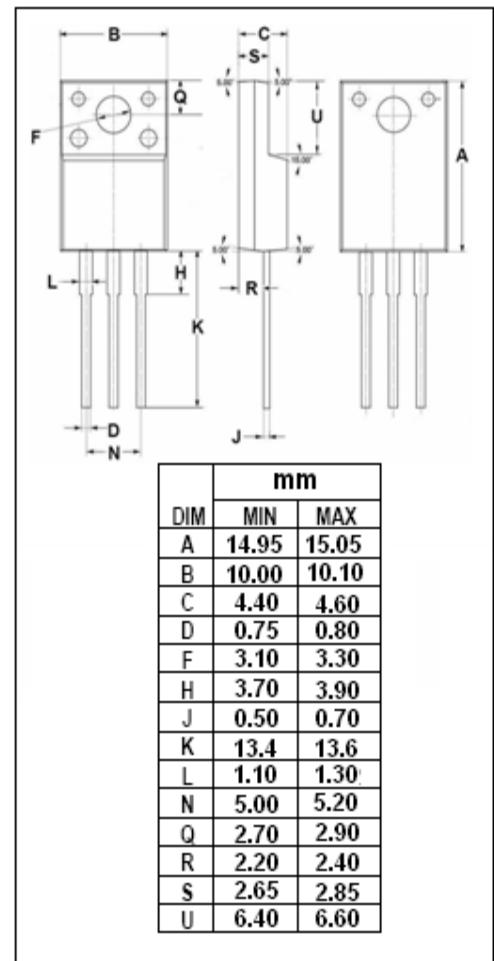


APPLICATIONS

- Power supplies, converters and power motor controls

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	250	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	10	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	40	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



N-Channel MOSFET Transistor
2SK1766
• ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}= 0$; $I_D= 1\text{mA}$	250		V
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}= V_{GS}$; $I_D=1\text{mA}$	1.5	3.5	V
$R_{DS(\text{on})}$	Drain-Source On-Resistance	$V_{GS}= 10\text{V}$; $I_D= 5\text{A}$		0.6	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}= \pm 30\text{V}$; $V_{DS}= 0$		± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}= 250\text{V}$; $V_{GS}= 0$		1	mA